



**INTEGRATED CIRCUITS, MONOLITHIC, CMOS
SILICON ON SAPPHIRE, 3.5GHz DELTA SIGMA
MODULATED FRACTIONAL-N PLL FREQUENCY
SYNTHESISER**

BASED ON TYPE PE33632

ESCC Detail Specification No. 9202/077

Issue 3	April 2014
---------	------------



LEGAL DISCLAIMER AND COPYRIGHT

European Space Agency, Copyright © 2014. All rights reserved.

The European Space Agency disclaims any liability or responsibility, to any person or entity, with respect to any loss or damage caused, or alleged to be caused, directly or indirectly by the use and application of this ESCC publication.

This publication, without the prior permission of the European Space Agency and provided that it is not used for a commercial purpose, may be:

- copied in whole, in any medium, without alteration or modification.
- copied in part, in any medium, provided that the ESCC document identification, comprising the ESCC symbol, document number and document issue, is removed.

DOCUMENTATION CHANGE NOTICE

(Refer to <https://escies.org> for ESCC DCR content)

DCR No.	CHANGE DESCRIPTION
849	Specification upissued to incorporate editorial changes per DCR.

TABLE OF CONTENTS

1	GENERAL	6
1.1	SCOPE	6
1.2	APPLICABLE DOCUMENTS	6
1.3	TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS	6
1.4	THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS	6
1.4.1	The ESCC Component Number	6
1.4.2	Component Type Variants	6
1.5	MAXIMUM RATINGS	6
1.6	HANDLING PRECAUTIONS	7
1.7	PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION	8
1.7.1	Ceramic Quad Flat Package J-BEND (CQFPJ-68) - 68 Terminals	8
1.8	FUNCTIONAL DIAGRAM	9
1.9	PIN ASSIGNMENT AND DESCRIPTION	10
1.10	FUNCTIONAL DESCRIPTION	14
1.10.1	Overview	14
1.10.2	Main Counter Chain	14
1.10.2.1	Normal Operating Mode	14
1.10.2.2	Prescaler Bypass Mode	15
1.10.3	Reference Counter Chain	15
1.10.4	Register Programming	15
1.10.4.1	Serial Interface Mode	15
1.10.4.2	Direct Interface Mode	16
1.10.4.3	Enhancement Register	17
1.10.5	Phase Detector	17
1.11	INPUT AND OUTPUT PROTECTION NETWORKS	18
2	REQUIREMENTS	19
2.1	GENERAL	19
2.1.1	Deviations from the Generic Specification	19
2.1.1.1	Deviations from Screening Tests - Chart F3	19
2.2	MARKING	19
2.3	ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES	19
2.3.1	Room Temperature Electrical Measurements	19
2.3.2	High and Low Temperatures Electrical Measurements	31
2.4	PARAMETER DRIFT VALUES	31
2.5	INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS	32



2.6	POWER BURN-IN CONDITIONS	32
2.6.1	Electrical Test Conditions	32
2.6.2	Environmental Test Conditions	32
2.6.3	Burn-in Stimulus	33
2.6.4	Burn-in Schematic	34
2.7	OPERATING LIFE CONDITIONS	35
2.8	TOTAL DOSE RADIATION TESTING	35
2.8.1	Bias Conditions and Total Dose Level for Total Dose Radiation Testing	35
2.8.2	Electrical Measurements for Total Dose Radiation Testing	37
	APPENDIX 'A'	38

1 GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 9000.
- (b) MIL-STD-883, Test Methods and Procedures for Microelectronics.

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 920207701R

- Detail Specification Reference: 9202077
- Component Type Variant Number: 01
- Total Dose Radiation Level Letter: R (as required)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead/Terminal Material and Finish	Weight max g	Total Dose Radiation Level Letter
01	PE33632	CQFPJ-68	G2	10	R [100kRAD(Si)]

The lead/terminal material and finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

Total dose radiation level letters are defined in ESCC Basic Specification No. 22900. If an alternative radiation test level is specified in the Purchase Order the letter shall be changed accordingly.

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage. Prolonged use of the device at the maximum ratings may reduce the device's overall reliability.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Units	Remarks
Supply Voltage Range	V_{DD}	-0.3 to 4	V	Note 1
Input Voltage Range	V_{IN}	-0.3 to $V_{DD}+0.3$	V	Note 2
DC Input Current Range	I_{IN}	-10 to +10	mA	
DC Output Current Range	I_{OUT}	-90 to +110	mA	Note 3
Device Power Dissipation (Continuous)	P_D	500	mW	
Operating Temperature Range	T_{op}	-40 to +85	°C	T_{amb}
Storage Temperature Range	T_{stg}	-65 to +150	°C	
Junction Temperature	T_j	+150	°C	
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	15	°C/W	
Soldering Temperature	T_{sol}	+260	°C	Note 4

NOTES:

1. All voltages are with respect to V_{SS} . Device is functional for $2.85 \leq V_{DD} \leq 3.45V$.
2. $V_{DD} + 0.3V$ shall not exceed 4V.
3. The maximum output current of any single output for a maximum duration of 1 second.
4. Duration 10 seconds maximum at a distance of not less than 1.6mm from the device body and the same terminal shall not be re-soldered until 3 minutes have elapsed.

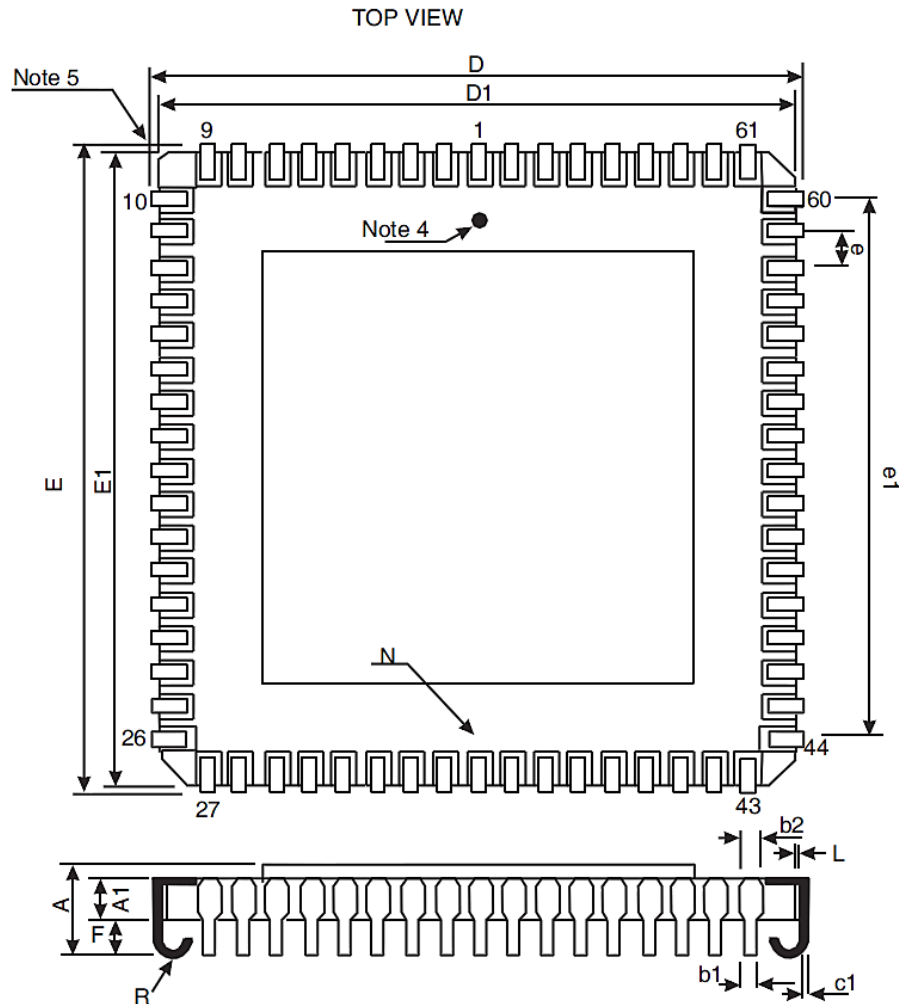
1.6 **HANDLING PRECAUTIONS**

These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling.

These components are categorised as Class 1 per ESCC Basic Specification No. 23800 with a minimum Critical Path Failure Voltage of 1000 Volts for all pins except DOUT, which has a minimum Critical Path Failure Voltage of 300 Volts. DOUT is a test pin only and does not affect functionality, operation or performance.

1.7 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.7.1 Ceramic Quad Flat Package J-BEND (CQFPJ-68) - 68 Terminals



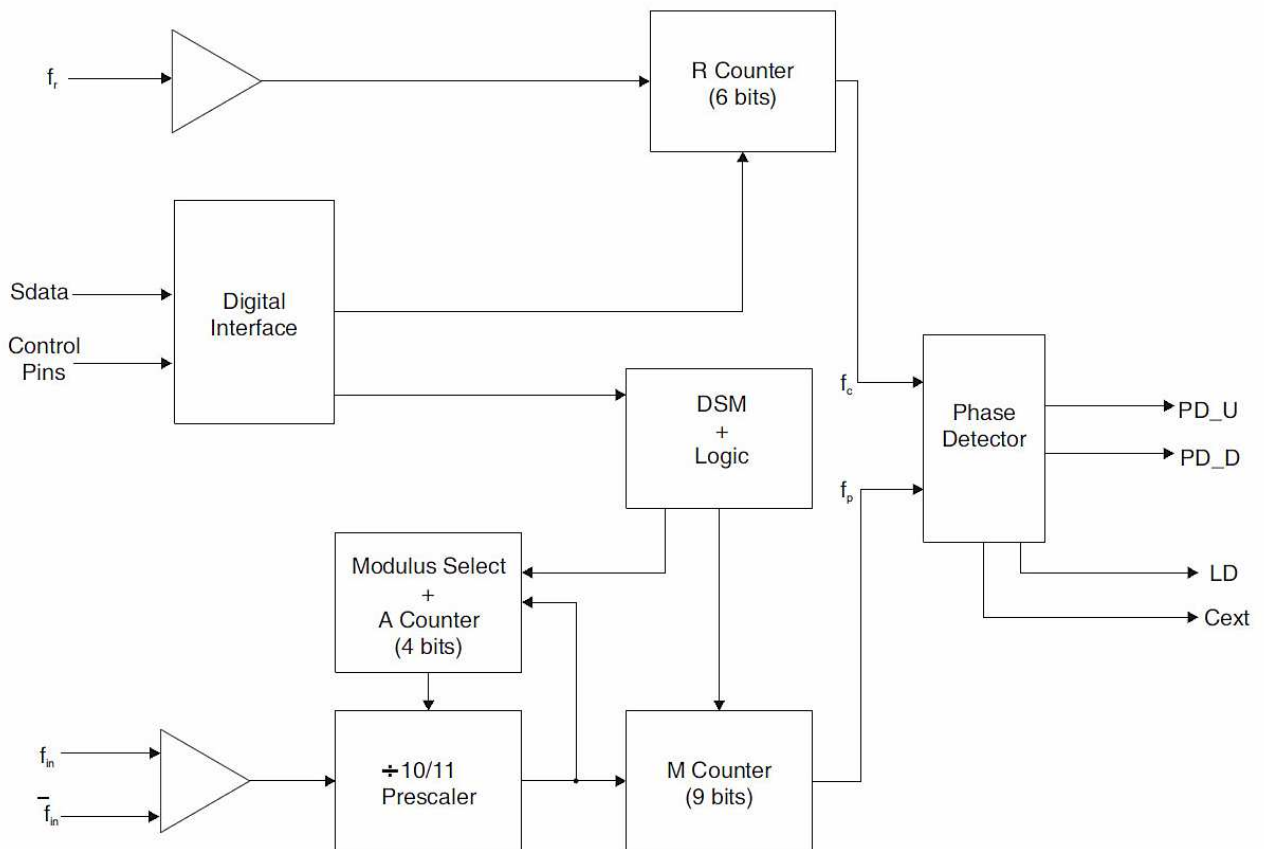
Symbols	Dimensions mm		Notes
	Min	Max	
A	3.124 TYPICAL		1
A1	1.82	2.24	
b1	0.432 TYPICAL		1
b2	0.762 TYPICAL		1
c1	0.152	0.254	1
D/E	24.89	25.4	
D1/E1	23.82	24.44	
e	1.27 BSC		1, 2
e1	20.06	20.58	3

Symbols	Dimensions mm		Notes
	Min	Max	
F	0.889 TYPICAL		1
L	0.508 TYPICAL		1
N	17 TERMINALS PER SIDE		3
R	0.762 TYPICAL		1, 6

NOTES:

1. Applies to all 68 terminals (17 per side).
2. 64 places. The true position pin spacing is 1.27mm between centrelines. Each pin centreline shall be located within $\pm 0.13\text{mm}$ of its true longitudinal position relative to the package centrelines.
3. 4 places.
4. A terminal identification mark shall be located in the region of Pin 1 as shown. Terminal numbers shall increase counter clockwise when viewed as shown starting from the centre terminal (Pin 1).
5. Index corner: Terminal identification is specified by reference to the index corner as shown.
6. Radius.

1.8 FUNCTIONAL DIAGRAM



1.9 PIN ASSIGNMENT AND DESCRIPTION

The table below describes each pin's assignment, type and standard, plus a brief description of its functionality.

Pin No.	Pin Name	Pin Type	Pin Standard	Valid Mode	Description
Top side					
1	R ₀	Input	CMOS	Direct	R Counter, bit 0 (LSB).
2	R ₁	Input	CMOS	Direct	R Counter, bit 1.
3	R ₂	Input	CMOS	Direct	R Counter, bit 2.
4	R ₃	Input	CMOS	Direct	R Counter, bit 3.
5	R ₄	Input	CMOS	Direct	R Counter, bit 4.
6	R ₅	Input	CMOS	Direct	R Counter, bit 5 (MSB).
7	K ₀	Input	CMOS	Direct	K Counter, bit 0 (LSB).
8	K ₁	Input	CMOS	Direct	K Counter, bit 1.
9	V _{SS}	Ground	-	-	V _{SS}
Left-hand side					
10	V _{DD}	Power	-	-	Digital core V _{DD} (Note 1).
11	K ₂	Input	CMOS	Direct	K Counter, bit 2.
12	K ₃	Input	CMOS	Direct	K Counter, bit 3.
13	K ₄	Input	CMOS	Direct	K Counter, bit 4.
14	K ₅	Input	CMOS	Direct	K Counter, bit 5.
15	K ₆	Input	CMOS	Direct	K Counter, bit 6.
16	K ₇	Input	CMOS	Direct	K Counter, bit 7.
17	K ₈	Input	CMOS	Direct	K Counter, bit 8.
18	K ₉	Input	CMOS	Direct	K Counter, bit 9.
19	K ₁₀	Input	CMOS	Direct	K Counter, bit 10.
20	K ₁₁	Input	CMOS	Direct	K Counter, bit 11.
21	K ₁₂	Input	CMOS	Direct	K Counter, bit 12.
22	K ₁₃	Input	CMOS	Direct	K Counter, bit 13.
23	K ₁₄	Input	CMOS	Direct	K Counter, bit 14.
24	K ₁₅	Input	CMOS	Direct	K Counter, bit 15.
25	K ₁₆	Input	CMOS	Direct	K Counter, bit 16.

Pin No.	Pin Name	Pin Type	Pin Standard	Valid Mode	Description
26	K ₁₇	Input	CMOS	Direct	K Counter, bit 17 (MSB).
Bottom side					
27	V _{DD}	Power	-	-	Digital core V _{DD} (Note 1).
28	V _{SS}	Ground	-	-	V _{SS}
29	M ₀	Input	CMOS	Direct	M Counter, bit 0 (LSB).
30	M ₁	Input	CMOS	Direct	M Counter, bit 1.
31	M ₂	Input	CMOS	Direct	M Counter, bit 2.
32	M ₃	Input	CMOS	Direct	M Counter, bit 3.
33	M ₄	Input	CMOS	Direct	M Counter, bit 4.
	S_WR			Serial	
34	M ₅	Input	CMOS	Direct	M Counter, bit 5.
	SDATA			Serial	
35	M ₆	Input	CMOS	Direct	M Counter, bit 6.
	SCLK			Serial	
36	M ₇	Input	CMOS	Direct	M Counter, bit 7.
37	M ₈	Input	CMOS	Direct	M Counter, bit 8 (MSB).
38	A ₀	Input	CMOS	Direct	A Counter, bit 0 (LSB).
39	A ₁	Input	CMOS	Direct	A Counter, bit 1.
	E_WR			Serial	
40	A ₂	Input	CMOS	Direct	A Counter, bit 2.
41	A ₃	Input	CMOS	Direct	A Counter, bit 3 (MSB).
42	DIRECT	Input	CMOS	Both	Direct mode select. "high" enables direct mode, "low" enables serial mode.

Pin No.	Pin Name	Pin Type	Pin Standard	Valid Mode	Description
43	PRE_EN	Input	CMOS	Direct	Prescaler enable, active "low". When "high", FIN bypasses the prescaler.
Right-hand side					
44	V _{DD}	Power	-	-	Digital core V _{DD} (Note 1).
45	V _{SS}	Ground	-	-	V _{SS}
46	V _{DD}	Power	-	-	Prescaler V _{DD} (Note 1).
47	FIN	Input	RF	Both	Prescaler input from the VCO. Maximum frequency 3.5GHz.
48	$\overline{\text{FIN}}$	Input	RF	Both	Prescaler complementary input. A bypass capacitor should be placed as close as possible to this pin and be connected in series with a 50Ω resistor directly to the ground plane.
49	V _{SS}	Ground	-	-	V _{SS}
50	CEXT	Output	CMOS (high resistance)	Both	Logical "NAND" of PD_U and PD_D terminated through an on-chip, 2kΩ series resistor. Connecting Cext to an external capacitor will low pass filter the input to the inverting amplifier used for driving LD.
51	LD	Output	Open Drain	Both	Lock detect and open drain logical inversion of Cext. When the loop is in lock, LD is high impedance, otherwise LD is a logic "low" ("0").
52	DOUT	Output	CMOS (low current)	Both	Data Out function, enabled in enhancement mode.
53	V _{DD}	Power	-	-	Output driver V _{DD} (Note 1).
54	V _{SS}	Ground	-	-	V _{SS}
55	PD_D	Output	CMOS	Both	PD_D pulses down when f _p leads f _c .
56	NC	-	-	-	Not Connected.
57	PD_U	Output	CMOS	Both	PD_U pulses down when f _c leads f _p .
58	V _{SS}	Ground	-	-	V _{SS}
59	V _{DD}	Power	-	-	Output driver V _{DD} (Note 1).
60	V _{DD}	Power	-	-	Phase detector V _{DD} (Note 1).
Top side					
61	V _{SS}	Ground	-	-	V _{SS}

Pin No.	Pin Name	Pin Type	Pin Standard	Valid Mode	Description
62	FR	Input	CMOS	Both	Reference frequency input.
63	V _{DD}	Power	-	-	Reference V _{DD} (Note 1).
64	V _{DD}	Power	-	-	Digital core V _{DD} (Note 1).
65	$\overline{\text{ENH}}$	Input	CMOS	Both	Enhancement mode. When asserted "low" ("0"), enhancement register bits are functional.
66	NC	-	-	-	Not Connected.
67	MS2_SEL	Input	CMOS	Both	MASH 1-1 select. "high" selects MASH 1-1 mode, "low" selects the MASH 1-1-1 mode.
68	RAND_EN	Input	CMOS	Both	K register LSB toggle enable. "high" enables the toggling of LSB. This is equivalent to having an additional bit for the LSB of K register. The frequency offset as a result of enabling this bit is the Phase Detector comparison frequency / 2 ¹⁹ .

NOTES:

1. All V_{DD} pins are connected by diodes and must be supplied with the same positive voltage level.
2. All digital input pins (i.e. CMOS inputs of Group 1 below) have a 70kΩ pull-down resistor to ground.

The table below describes the pin groups to be tested.

Group No.	Type	Total No. of Pins	Pin Numbers
1	CMOS Input with Pull-down	42	1 to 8, 11 to 26, 29 to 43, 65, 67 and 68
2	CMOS Input	1	62 (FR)
3	RF Input	2	47 (FIN) and 48 ($\overline{\text{FIN}}$)
4	High Current CMOS Output	2	55 (PD_D) and 57 (PD_U)
5	Low Current CMOS Output	1	52 (DOUT)
6	High Resistance CMOS Output	1	50 (CEXT)
7	Open Drain Output	1	51 (LD)
8	Power	9	10, 27, 44, 46, 53, 59, 60, 63 and 64
9	Ground	7	9, 28, 45, 49, 54, 58 and 61

1.10 FUNCTIONAL DESCRIPTION

1.10.1 Overview

The PE33632 consists of a prescaler, several counters, an 18-bit delta-sigma modulator (DSM) and a phase detector. The dual modulus prescaler divides the VCO frequency by either 10 or 11, depending on the value of the modulus select. Counters “R” and “M” divide the reference and prescaler outputs, respectively, by the integer values stored in a 20-bit register. An additional counter (“A”) is used in the modulus select logic. The DSM modulates the A Counter outputs in order to achieve the desired fractional step.

The phase-frequency detector generates up and down frequency control signals. Data is written into the internal registers via a three-wire serial bus. There are also various operational and test modes and a lock detect output.

1.10.2 Main Counter Chain

1.10.2.1 *Normal Operating Mode*

Setting the $\overline{\text{PRE_EN}}$ control bit “low” enables the $\div 10/11$ prescaler. The main counter chain then divides the RF input frequency (f_{in}) by an integer or fractional number derived from the values in the “M”, “A” Counters and the DSM input word K. The accumulator size is 18-bit, so the fractional value is fixed from the ratio $K/2^{18}$. There is an additional bit in the DSM that acts like an extra bit (19th bit). This bit is enabled by asserting the pin RAND_EN to “high”. Enabling this bit has the benefit of reducing the spurious levels. However, a small frequency offset will occur. This positive frequency offset is calculated with the following equation:

$$f_{\text{offset}} = (f_r / (R + 1)) / 2^{19} \quad (1)$$

All of the following equations do not take into account this frequency offset. If this offset is important to a specific frequency plan, appropriate account needs to be taken.

In the normal mode, the output from the main counter chain (f_p) is related to the VCO frequency (f_{in}) by the following equation:

$$f_p = f_{in} / [10 \times (M + 1) + A + K/2^{18}] \quad (2)$$

$$\text{Where } A \leq M + 1, 1 \leq M \leq 511$$

When the loop is locked, f_{in} is related to the reference frequency (f_r) by the following equation:

$$f_{in} = [10 \times (M + 1) + A + K/2^{18}] \times (f_r / (R + 1)) \quad (3)$$

$$\text{Where } A \leq M + 1, 1 \leq M \leq 511$$

A consequence of the upper limit on A is that f_{in} must be greater than or equal to $90 \times (f_r / (R + 1))$ to obtain contiguous channels. The A Counter can accept values as high as 15, but in typical operation it will cycle from 0 to 9 between increments in M.

Programming the M Counter with the minimum allowed value of “1” will result in a minimum M Counter divide ratio of “2”.

1.10.2.2 Prescaler Bypass Mode

Setting the frequency control register bit $\overline{\text{PRE_EN}}$ "high" allows f_{in} to bypass the $\div 10/11$ prescaler. In this mode, the prescaler and A Counter are powered down, and the input VCO frequency is divided by the M Counter directly. The following equation relates f_{in} to the reference frequency (f_r):

$$f_{in} = (M + 1) \times (f_r / (R + 1)) \quad (4)$$

Where $A \leq M + 1$, $1 \leq M \leq 511$

In this mode, neither the A Counter nor the K Counter is used and therefore only integer-N operation is possible.

1.10.3 Reference Counter Chain

The reference counter chain divides the reference frequency (f_r) down to the phase detector comparison frequency (f_c).

The output frequency of the 6-bit R Counter is related to the reference frequency by the following equation:

$$f_c = f_r / (R + 1) \quad (5)$$

Where $0 \leq R \leq 63$

Note that programming R with "0" will pass the reference frequency (f_r) directly to the phase detector.

1.10.4 Register Programming

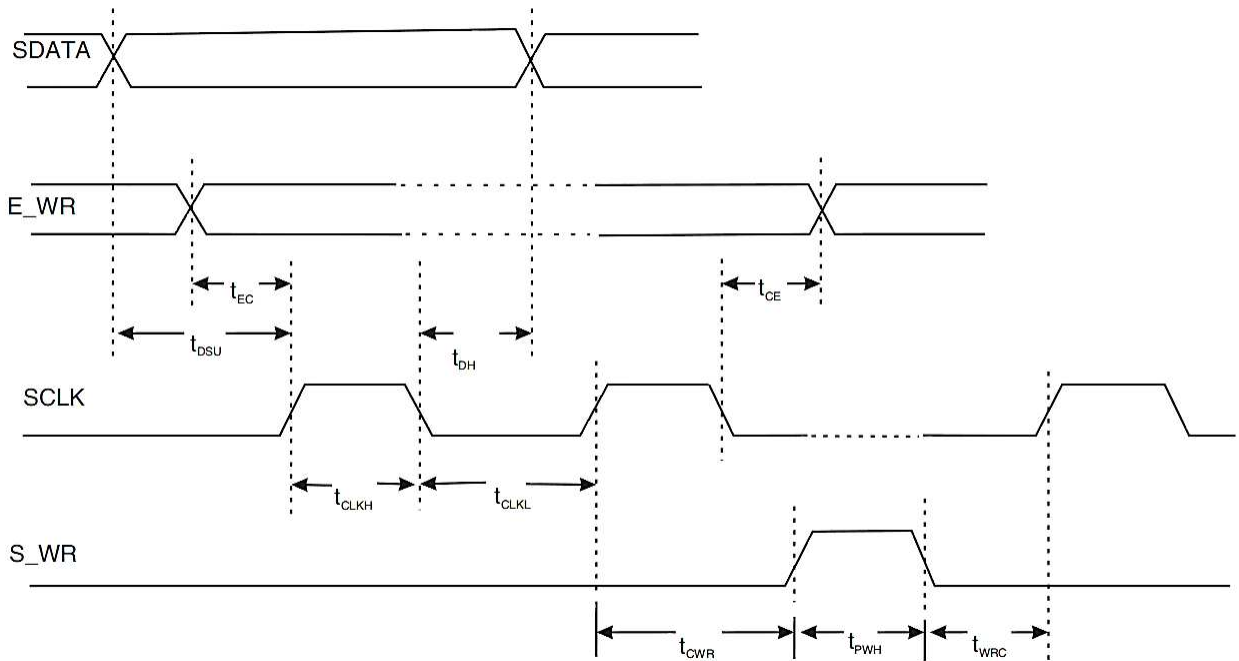
1.10.4.1 Serial Interface Mode

While the E_WR input is "low" and the S_WR input is "low", serial input data (SDATA input), B_0 to B_{20} , are clocked serially into the primary register on the rising edge of SCLK, MSB (B_0) first. The LSB is used as the address bit. When "0", the contents from the primary register are transferred to the secondary register on the rising edge of S_WR according to the timing chart shown below. When "1", data are transferred to the auxiliary register according to the same timing chart. The secondary register is used to program the various counters, while the auxiliary register is used to program the DSM.

Data are transferred to the counters as shown in the tables below.

While the E_WR input is "high" and the S_WR input is "low", serial input data (SDATA input), B_0 to B_7 , are clocked serially to the enhancement register on the rising edge of SCLK, MSB (B_0) first. The enhancement register is double buffered to prevent inadvertent control changes during serial loading, with buffer capture of the serially entered data performed on the falling edge of E_WR according to the timing chart shown below. After the falling edge of E_WR, the data provide control bits as shown in the tables below will have their bit functionality enabled by asserting the $\overline{\text{ENH}}$ input "low".

Serial Interface Timing Chart



1.10.4.2 *Direct Interface Mode*

Direct Interface Mode is selected by setting the DIRECT Input “high”. Counter control bits are set directly at the pins as shown in the tables below.

Secondary Register Programming

Interface Mode	\overline{ENH}	R ₅	R ₄	M ₈	M ₇	$\overline{PRE_EN}$	M ₆	M ₅	M ₄	M ₃	M ₂	M ₁	M ₀	R ₃	R ₂	R ₁	R ₀	A ₃	A ₂	A ₁	A ₀	Address
Direct	1	R ₅	R ₄	M ₈	M ₇	$\overline{PRE_EN}$	M ₆	M ₅	M ₄	M ₃	M ₂	M ₁	M ₀	R ₃	R ₂	R ₁	R ₀	A ₃	A ₂	A ₁	A ₀	X
Serial (1)	1	B ₀	B ₁	B ₂	B ₃	B ₄	B ₅	B ₆	B ₇	B ₈	B ₉	B ₁₀	B ₁₁	B ₁₂	B ₁₃	B ₁₄	B ₁₅	B ₁₆	B ₁₇	B ₁₈	B ₁₉	0

↑ MSB (first in)

LSB (last in) ↑

Auxiliary Register Bit Programming

Interface Mode	\overline{ENH}	K ₁₇	K ₁₆	K ₁₅	K ₁₄	K ₁₃	K ₁₂	K ₁₁	K ₁₀	K ₉	K ₈	K ₇	K ₆	K ₅	K ₄	K ₃	K ₂	K ₁	K ₀	Reserved	Address	
Direct	1	K ₁₇	K ₁₆	K ₁₅	K ₁₄	K ₁₃	K ₁₂	K ₁₁	K ₁₀	K ₉	K ₈	K ₇	K ₆	K ₅	K ₄	K ₃	K ₂	K ₁	K ₀	X	X	X
Serial (1)	1	B ₀	B ₁	B ₂	B ₃	B ₄	B ₅	B ₆	B ₇	B ₈	B ₉	B ₁₀	B ₁₁	B ₁₂	B ₁₃	B ₁₄	B ₁₅	B ₁₆	B ₁₇	B ₁₈	B ₁₉	1

↑ MSB (first in)

LSB (last in) ↑

Enhancement Register Programming

Interface Mode	$\overline{\text{ENH}}$	Reserved	Reserved	FP Output	Power Down	Counter Load	MSEL Output	FC Output	LD Disable
Serial (2)	0	B ₀	B ₁	B ₂	B ₃	B ₄	B ₅	B ₆	B ₇

↑ MSB (first in)

LSB (last in) ↑

NOTES:

1. Serial data clocked serially on SCLK rising edge while E_WR “low” and captured in secondary register on S_WR rising edge.
2. Serial data clocked serially on SCLK rising edge while E_WR “high” and captured in double buffer on E_WR falling edge.

1.10.4.3 Enhancement Register

The functions of the enhancement register bits are shown below with all bits active “high”.

Bit Number	Bit Function	Description
0	Reserved	Reserve bit - program to 0.
1	Reserved	Reserve bit - program to 0.
2	FP Output	Drives the M Counter output onto the DOUT output.
3	Power Down	Power down of all functions except programming interface.
4	Counter Load	Immediate and continuous load of counter programming.
5	MSEL Output	Drives the internal dual modulus prescaler modulus select (MSEL) output onto the DOUT output.
6	FC Output	Drives the reference counter output onto the DOUT output.
7	LD Disable	Disables the LD pin for quieter operation.

1.10.5 Phase Detector

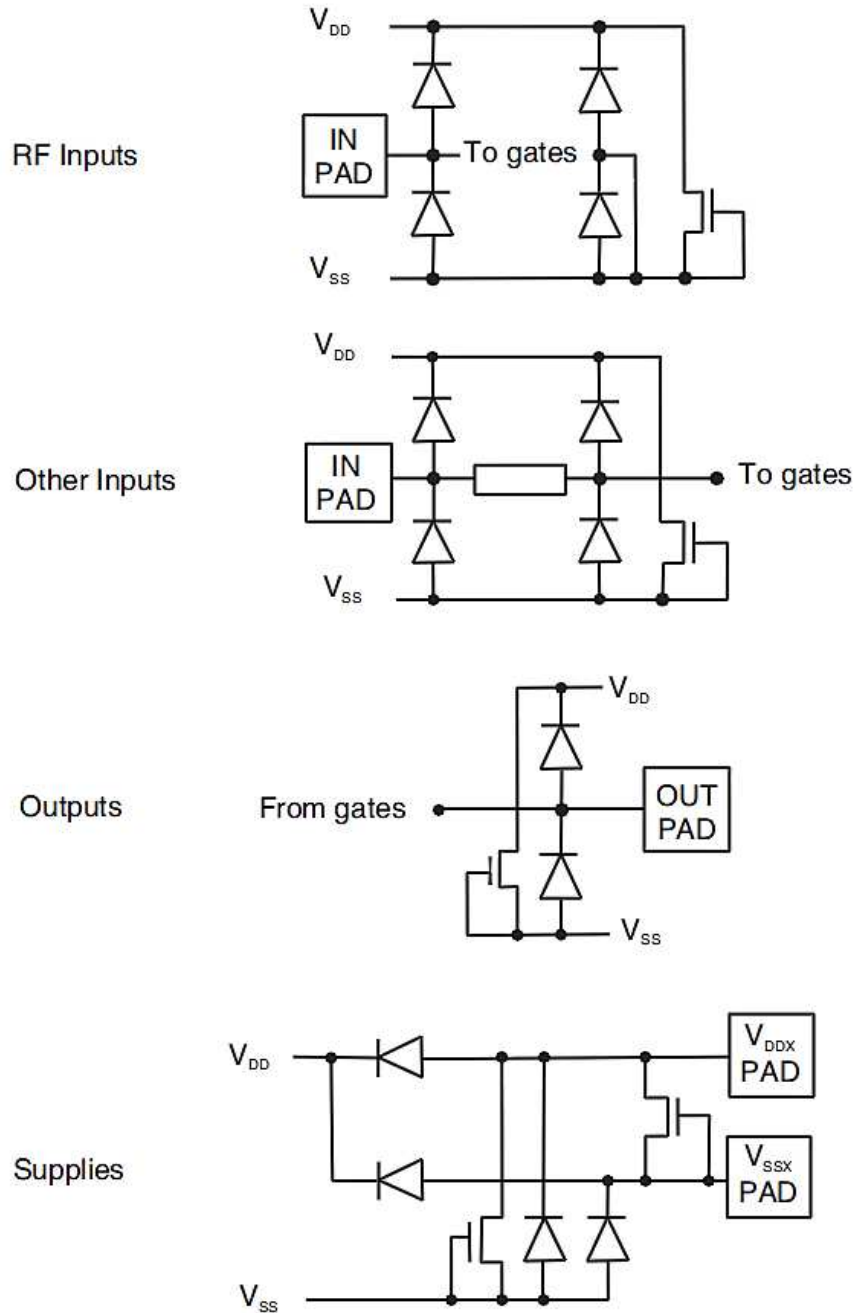
The phase detector is triggered by rising edges from the main Counter (f_p) and the reference Counter (f_c). It has two outputs, namely PD_U and PD_D. If the divided VCO leads the divided reference in phase or frequency (f_p leads f_c), PD_D pulses “low”. If the divided reference leads the divided VCO in phase or frequency (f_c leads f_p), PD_U pulses “low”. The width of either pulse is directly proportional to phase offset between the two input signals, f_p and f_c .

For the UP and DOWN mode, PD_U and PD_D drive an active loop filter which controls the VCO tune voltage. The phase detector gain is equal to $V_{DD}/2\pi$.

PD_U pulses cause an increase in VCO frequency and PD_D pulses cause a decrease in VCO frequency, for a positive K_v VCO.

A “lock detect” output, LD, is also provided via the pin CEXT. CEXT is the logical “NAND” of PD_U and PD_D waveforms, which is driven through a serial 2kΩ resistor. Connecting CEXT to an external shunt capacitor provides low pass filtering of this signal. CEXT also drives the input of an internal inverting comparator with an open drain output. Thus LD is an “AND” function of PD_U and PD_D.

1.11 INPUT AND OUTPUT PROTECTION NETWORKS



2 REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

2.1.1.1 Deviations from Screening Tests - Chart F3

High Temperature Reverse Bias Burn-in and the subsequent Final Measurements for HTRB Burn-in shall be omitted.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) Terminal identification.
- (b) The ESCC qualified components symbol (for ESCC qualified components only).
- (c) The ESCC Component Number.
- (d) Traceability information.

2.3 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

Electrical measurements shall be performed at room, high and low temperatures.

2.3.1 Room Temperature Electrical Measurements

The measurements shall be performed at $T_{amb} = +22 \pm 3 \text{ }^\circ\text{C}$.

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
Input Clamp Voltage to V_{SS}	V_{ICL}	3022	Inputs: Pin Groups 1 to 3 Outputs: Pin Groups 4 to 7 $V_{DD} = V_{SS} = 0V$ $I_{IN} = 200\mu A$ Note 1	-1.5	-	V
Input Clamp Voltage to V_{DD}	V_{ICH}	3022	Inputs: Pin Groups 1 to 3 Outputs: Pin Groups 4 to 7 $V_{DD} = V_{SS} = 0V$ $I_{IN} = -200\mu A$ Note 1	-	1.5	V

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
Shorts / Continuity Check	V_{SH}	-	Inputs: Pin Groups 1 to 3 Outputs: Pin Groups 4 to 7 $V_{DD} = V_{SS} = 0V$ $I_{IN} = -200\mu A$ Note 1	-	200	mV
Standby Supply Current with Prescaler	I_{DDQ1}	3005	$V_{DD} = 3.45V, V_{SS} = 0V$ Use pattern <i>mode</i> , stop at label <i>pdwn_sp</i> Note 3	-	500	μA
Dynamic Supply Current with Prescaler	$I_{DDOPENA}$	3005	$V_{DD} = 3.45V, V_{SS} = 0V$ $V_{IH} = 3.45V, V_{IL} = 0V$ (Pin Groups 1 to 3) $V_{OH} = 1.8V, V_{OL} = 1.3V$ $I_{OL} = I_{OH} = 0A$ (Pin Groups 4 to 6) $I_{OL} = -1mA$ (Pin Group 7) $C_{LOAD} < 62pF$ Use pattern <i>main_pattern @ 10 MHz</i> Loop from first to last vector Note 2	20	45	mA
Dynamic Supply Current without Prescaler	$I_{DDOPDIS}$	3005	$V_{DD} = 3.45V, V_{SS} = 0V$ $V_{IH} = 3.45V, V_{IL} = 0V$ (Pin Groups 1 to 3) $V_{OH} = 1.8V, V_{OL} = 1.3V$ $I_{OL} = I_{OH} = 0A$ (Pin Groups 4 to 6) $I_{OL} = -1mA$ (Pin Group 7) $C_{LOAD} < 62pF$ Use pattern <i>main_pattern @ 10 MHz</i> Loop from first to last vector Note 2	8	20	mA

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
Functional Test, Typical Voltage (Relaxed Limits)	-	3014	$V_{DD} = 3.3V$, $V_{SS} = 0V$ $V_{IH} = 3.3V$, $V_{IL} = 0V$ (Pin Groups 1 to 3) $V_{OH} = 1.8V$, $V_{OL} = 1.3V$ $I_{OL} = I_{OH} = 0A$ (Pin Groups 4 to 6) $I_{OL} = 0A$ (Pin Group 7) $C_{LOAD} < 62pF$ Use patterns <i>main_pattern</i> (between labels "main_st" and "end_u_d") and <i>dsm_p1 @ 10 MHz</i> Note 4	Go/NoGo		-
Functional Test, Minimum Voltage (Specified Limits)	-	3014	$V_{DD} = 2.85V$, $V_{SS} = 0V$ $V_{IH} = 1.98V$, $V_{IL} = 870mV$ (Pin Groups 1 and 2) $V_{IH} = 2.85V$, $V_{IL} = 0V$ (Pin Group 3) $V_{OH} = 2.465V$, $V_{OL} = 385mV$ (Pin Groups 4 to 7) $I_{OL}/I_{OH} = -3/+6mA$ (Pin Group 4) $I_{OL}/I_{OH} = \pm 200\mu A$ (Pin Group 5) $I_{OL}/I_{OH} = \pm 100\mu A$ (Pin Group 6) $I_{OL} = -1mA$ (Pin Group 7) $C_{LOAD} < 62pF$ Use patterns <i>main_pattern</i> (between labels "main_st" and "end_u_d") and <i>dsm_p1 @ 10 MHz</i> Note 4	Go/NoGo		-

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
Functional Test, Maximum Voltage (Specified Limits)	-	3014	$V_{DD} = 3.45V$, $V_{SS} = 0V$ $V_{IH} = 2.4V$, $V_{IL} = 1.05V$ (Pin Groups 1 and 2) $V_{IH} = 3.45V$, $V_{IL} = 0V$ (Pin Group 3) $V_{OH} = 3.065V$, $V_{OL} = 385mV$ (Pin Groups 4 to 7) $I_{OL}/I_{OH} = -3/+6mA$ (Pin Group 4) $I_{OL}/I_{OH} = \pm 200\mu A$ (Pin Group 5) $I_{OL}/I_{OH} = \pm 100\mu A$ (Pin Group 6) $I_{OL} = -1mA$ (Pin Group 7) $C_{LOAD} < 62pF$ Use patterns <i>main_pattern</i> (between labels "main_st" and "end_u_d") and <i>dsm_p1</i> @ 10 MHz Note 4	Go/NoGo		-
CMOS Input Voltage, Low Level (Minimum V_{DD})	V_{IL1}	-	Pin Groups 1 and 2 $V_{DD} = 2.85V$, $V_{SS} = 0V$ Use pattern <i>main_pattern</i> Note 5	855	-	mV
CMOS Input Voltage, High Level (Minimum V_{DD})	V_{IH1}	-	Pin Groups 1 and 2 $V_{DD} = 2.85V$, $V_{SS} = 0V$ Use pattern <i>main_pattern</i> Note 5	-	1995	mV
CMOS Output Voltage, Low Level (High Current Buffer at Minimum V_{DD})	V_{OL1_H}	3007	Pin Group 4 $V_{DD} = 2.85V$, $V_{SS} = 0V$ $I_{OL} = -6mA$ Use pattern <i>main_pattern</i> Note 6	-	400	mV
CMOS Output Voltage, Low Level (Low Current Buffer at Minimum V_{DD})	V_{OL1_L}	3007	Pin Group 5 $V_{DD} = 2.85V$, $V_{SS} = 0V$ $I_{OL} = -200\mu A$ Use pattern <i>main_pattern</i> Note 6	-	400	mV
CMOS Output Voltage, Low Level (Buffer with Serial Resistor at Minimum V_{DD})	V_{OL1_R}	3007	Pin Group 6 $V_{DD} = 2.85V$, $V_{SS} = 0V$ $I_{OL} = -100\mu A$ Use pattern <i>main_pattern</i> Note 6	-	400	mV

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
CMOS Output Voltage, Low Level (Open Drain Buffer at Minimum V_{DD})	V_{OL1_OD}	3007	Pin Group 7 $V_{DD} = 2.85V$, $V_{SS} = 0V$ $I_{OL} = -1mA$ Use pattern <i>main_pattern</i> Note 6	-	400	mV
CMOS Output Voltage, Low Level (High Current Buffer at Maximum V_{DD})	V_{OL2_H}	3007	Pin Group 4 $V_{DD} = 3.45V$, $V_{SS} = 0V$ $I_{OL} = -6mA$ Use pattern <i>main_pattern</i> Note 6	-	400	mV
CMOS Output Voltage, Low Level (Low Current Buffer at Maximum V_{DD})	V_{OL2_L}	3007	Pin Group 5 $V_{DD} = 3.45V$, $V_{SS} = 0V$ $I_{OL} = -200\mu A$ Use pattern <i>main_pattern</i> Note 6	-	400	mV
CMOS Output Voltage, Low Level (Buffer with Serial Resistor at Maximum V_{DD})	V_{OL2_R}	3007	Pin Group 6 $V_{DD} = 3.45V$, $V_{SS} = 0V$ $I_{OL} = -100\mu A$ Use pattern <i>main_pattern</i> Note 6	-	400	mV
CMOS Output Voltage, Low Level (Open Drain Buffer at Maximum V_{DD})	V_{OL2_OD}	3007	Pin Group 7 $V_{DD} = 3.45V$, $V_{SS} = 0V$ $I_{OL} = -1mA$ Use pattern <i>main_pattern</i> Note 6	-	400	mV
CMOS Output Voltage, High Level (High Current Buffer at Minimum V_{DD})	V_{OH1_H}	3006	Pin Group 4 $V_{DD} = 2.85V$, $V_{SS} = 0V$ $I_{OH} = 3mA$ Use pattern <i>main_pattern</i> Note 6	2.25	-	V
CMOS Output Voltage, High Level (Low Current Buffer at Minimum V_{DD})	V_{OH1_L}	3006	Pin Group 5 $V_{DD} = 2.85V$, $V_{SS} = 0V$ $I_{OH} = 200\mu A$ Use pattern <i>main_pattern</i> Note 6	2.25	-	V
CMOS Output Voltage, High Level (Buffer with Serial Resistor at Minimum V_{DD})	V_{OH1_R}	3006	Pin Group 6 $V_{DD} = 2.85V$, $V_{SS} = 0V$ $I_{OH} = 100\mu A$ Use pattern <i>main_pattern</i> Note 6	2.25	-	V

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
CMOS Output Voltage, High Level (High Current Buffer at Maximum V_{DD})	V_{OH2_H}	3006	Pin Group 4 $V_{DD} = 3.45V$, $V_{SS} = 0V$ $I_{OH} = 3mA$ Use pattern <i>main_pattern</i> Note 6	3.05	-	V
CMOS Output Voltage, High Level (Low Current Buffer at Maximum V_{DD})	V_{OH2_L}	3006	Pin Group 5 $V_{DD} = 3.45V$, $V_{SS} = 0V$ $I_{OH} = 200\mu A$ Use pattern <i>main_pattern</i> Note 6	3.05	-	V
CMOS Output Voltage, High Level (Buffer with Serial Resistor at Maximum V_{DD})	V_{OH2_R}	3006	Pin Group 6 $V_{DD} = 3.45V$, $V_{SS} = 0V$ $I_{OH} = 100\mu A$ Use pattern <i>main_pattern</i> Note 6	3.05	-	V
CMOS Input Leakage Current, Low Level (with Pull-down)	I_{IL_PD}	3009	Pin Group 1 $V_{DD} = 3.45V$ $V_{SS} = 0V$ $V_{IN}(\text{Under Test}) = 0V$ $V_{IN}(\text{Remaining Inputs}) = 3.45V$	-250	250	nA
CMOS Input Leakage Current, Low Level	I_{IL}	3009	Pin Group 2 $V_{DD} = 3.45V$ $V_{SS} = 0V$ $V_{IN}(\text{Under Test}) = 0V$ $V_{IN}(\text{Remaining Inputs}) = 3.45V$	-15	-50	μA
CMOS Input Leakage Current, High Level (with Pull-down)	I_{IH_PD}	3010	Pin Group 1 $V_{DD} = 3.45V$ $V_{SS} = 0V$ $V_{IN}(\text{Under Test}) = 3.45V$ $V_{IN}(\text{Remaining Inputs}) = 0V$	30	75	μA
CMOS Input Leakage Current, High Level	I_{IH}	3010	Pin Group 2 $V_{DD} = 3.45V$ $V_{SS} = 0V$ $V_{IN}(\text{Under Test}) = 3.45V$ $V_{IN}(\text{Remaining Inputs}) = 0V$	15	50	μA
High-Impedance Output Leakage Current, High Level	I_{OZH}	3021	Pin Group 7 $V_{DD} = 3.45V$, $V_{SS} = 0V$ $V_{OUT} = 3.45V$ Use pattern <i>main_pattern</i> , stop at label "I _{lzh} " Note 7	-	10	μA

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
Serial Clock Minimum Pulse Width High (Minimum V_{DD})	t_{CLKH1}	3003	$V_{DD} = 2.85V, V_{SS} = 0V$ From posedge SCLK (↑ #35) to negedge SCLK (↓ #35) Use pattern <i>main_pattern</i> Note 10	-	30	ns
Serial Clock Minimum Pulse Width Low (Minimum V_{DD})	t_{CLKL1}	3003	$V_{DD} = 2.85V, V_{SS} = 0V$ From negedge SCLK (↓ #35) to posedge SCLK (↑ #35) Use pattern <i>main_pattern</i> Note 10	-	30	ns
Serial Data to Serial Clock Setup Time (Minimum V_{DD})	t_{DSU1}	3003	$V_{DD} = 2.85V, V_{SS} = 0V$ From any edge of SDATA (#34) to posedge SCLK (↑ #35) Use pattern <i>main_pattern</i> Note 10	-	10	ns
Serial Data to Serial Clock Hold Time (Minimum V_{DD})	t_{DH1}	3003	$V_{DD} = 2.85V, V_{SS} = 0V$ From posedge SCLK (↑ #35) to any edge of SDATA (#34) Use pattern <i>main_pattern</i> Note 10	-	10	ns
Serial Load Minimum Pulse Width High (Minimum V_{DD})	t_{PWH1}	3003	$V_{DD} = 2.85V, V_{SS} = 0V$ From posedge S_WR (↑ #33) to negedge S_WR (↓ #33) Use pattern <i>main_pattern</i> Note 10	-	30	ns
Serial Clock Rising Edge to Serial Load Rising Edge (Minimum V_{DD})	t_{CWR1}	3003	$V_{DD} = 2.85V, V_{SS} = 0V$ From posedge SCLK (↑ #35) to posedge S_WR (↑ #33) Use pattern <i>main_pattern</i> Note 10	-	30	ns
Serial Clock Falling Edge to Enhancement Write Transition (Minimum V_{DD})	t_{CE1}	3003	$V_{DD} = 2.85V, V_{SS} = 0V$ From negedge SCLK (↓ #35) to any edge of E_WR (#39) Use pattern <i>main_pattern</i> Note 10	-	30	ns

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
Serial Load Falling Edge to Serial Clock Rising Edge (Minimum V_{DD})	t_{WRC1}	3003	$V_{DD} = 2.85V, V_{SS} = 0V$ From negedge S_WR (↓ #33) to posedge SCLK (↑ #35) Use pattern <i>main_pattern</i> Note 10	-	30	ns
Enhancement Transition to Serial Clock Rising Edge (Minimum V_{DD})	t_{EC1}	3003	$V_{DD} = 2.85V, V_{SS} = 0V$ From any edge of E_WR (#39) to posedge SCLK (↑ #35) Use pattern <i>main_pattern</i> Note 10	-	30	ns
Reference Clock Input Sensitivity	S_{FR}	-	$V_{DD} = 2.85V, V_{SS} = 0V$ $f_{IN} = 100\text{ MHz}$ Use pattern <i>mode</i> , stop at label <i>mode_sp2</i> Note 11	-	-5	dBm
Prescaler Input Sensitivity (Minimum f_{IN})	S_{FIN250}	-	$V_{DD} = 2.85V, V_{SS} = 0V$ $f_{IN} = 250\text{ MHz}$ Use pattern <i>mode</i> , stop at label <i>mode_sp2</i> Note 11	-	-5	dBm
Prescaler Input Sensitivity (Medium 1 f_{IN})	S_{FIN300}	-	$V_{DD} = 2.85V, V_{SS} = 0V$ $f_{IN} = 300\text{ MHz}$ Use pattern <i>mode</i> , stop at label <i>mode_sp2</i> Note 11	-	-5	dBm
Prescaler Input Sensitivity (Medium 2 f_{IN})	S_{FIN500}	-	$V_{DD} = 2.85V, V_{SS} = 0V$ $f_{IN} = 500\text{ MHz}$ Use pattern <i>mode</i> , stop at label <i>mode_sp2</i> Note 11	-	-5	dBm
Prescaler Input Sensitivity (Medium 3 f_{IN})	$S_{FIN1000}$	-	$V_{DD} = 2.85V, V_{SS} = 0V$ $f_{IN} = 1000\text{ MHz}$ Use pattern <i>mode</i> , stop at label <i>mode_sp2</i> Note 11	-	-5	dBm
Prescaler Input Sensitivity (Medium 4 f_{IN})	$S_{FIN2000}$	-	$V_{DD} = 2.85V, V_{SS} = 0V$ $f_{IN} = 2000\text{ MHz}$ Use pattern <i>mode</i> , stop at label <i>mode_sp2</i> Note 11	-	-5	dBm

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
Prescaler Input Sensitivity (Medium $5 f_{IN}$)	$S_{FIN3000}$	-	$V_{DD} = 2.85V, V_{SS} = 0V$ $f_{IN} = 3000 \text{ MHz}$ Use pattern <i>mode</i> , stop at label <i>mode_sp2</i> Note 11	-	-5	dBm
Prescaler Input Sensitivity (Maximum f_{IN})	$S_{FIN3250}$	-	$V_{DD} = 2.85V, V_{SS} = 0V$ $f_{IN} = 3250 \text{ MHz}$ Use pattern <i>mode</i> , stop at label <i>mode_sp2</i> Note 11	-	-5	dBm
Prescaler Input Sensitivity (Maximum f_{IN} , Typical V_{DD})	$S_{FIN3300}$	-	$V_{DD} = 3.15V, V_{SS} = 0V$ $f_{IN} = 3300 \text{ MHz}$ Use pattern <i>mode</i> , stop at label <i>mode_sp2</i> Note 11	-	0	dBm
Prescaler Input Sensitivity ($>$ Maximum f_{IN} , Typical V_{DD})	$S_{FIN3550}$	-	$V_{DD} = 3.15V, V_{SS} = 0V$ $f_{IN} = 3550 \text{ MHz}$ Use pattern <i>mode</i> , stop at label <i>mode_sp2</i> Note 11	-	0	dBm
Supply Current during Phase Noise Measurements, Typical Low V_{DD}	$I_{DDOPPN1}$	3005	$V_{DD} = 3V, V_{SS} = 0V$ Note 13	5	80	mA
Supply Current during Phase Noise Measurements, Typical High V_{DD}	$I_{DDOPPN2}$	3005	$V_{DD} = 3.3V, V_{SS} = 0V$ Note 13	5	80	mA
Phase Noise @ 100 Hz Offset, Typical Low V_{DD}	PN_{1001}	-	$V_{DD} = 3V, V_{SS} = 0V$ Note 12	-95	-70	dBc/Hz
Phase Noise @ 1 kHz Offset, Typical Low V_{DD}	PN_{1K1}	-	$V_{DD} = 3V, V_{SS} = 0V$ Note 12	-101	-81	dBc/Hz
Phase Noise @ 10 kHz Offset, Typical Low V_{DD}	PN_{10K1}	-	$V_{DD} = 3V, V_{SS} = 0V$ Note 12	-107	-89	dBc/Hz
Phase Noise @ 100 Hz Offset, Typical High V_{DD}	PN_{1002}	-	$V_{DD} = 3.3V, V_{SS} = 0V$ Note 12	-95	-83	dBc/Hz
Phase Noise @ 1 kHz Offset, Typical High V_{DD}	PN_{1K2}	-	$V_{DD} = 3.3V, V_{SS} = 0V$ Note 12	-101	-91	dBc/Hz

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
Phase Noise @ 10 kHz Offset, Typical High V_{DD}	PN _{10K2}	-	$V_{DD} = 3.3V, V_{SS} = 0V$ Note 12	-107	-96	dBc/Hz

NOTES:

1. Continuity test
Comparison limit value, no measurement value recorded.
2. Dynamic current
For measurement of the dynamic current, the pattern *main_pattern* is used and loops from first to last vector. Instantaneous current is measured and recorded (without any link to a specific vector number). Total combined current for all V_{DD} pins. During the test, outputs are loaded with a capacitive load < 62 pF (tester load) but without active load. Comparators are disabled during this test.
3. Quiescent current
During quiescent current test, outputs are loaded without active current load but with a capacitive load < 62 pF (tester load).
The measurement is performed with the device having been initialised using pattern mode, stopped at end of vector labelled *pdwn_sp*. Total combined current of all V_{DD} pins.
The measurement accuracy is better than 1µA.
4. Functional test
During functional test, outputs are loaded with an active current load (when specified) and a capacitive load < 62 pF (tester load). For the active current load, the threshold load switching is set to $V_{DD}/2$.
Output comparison is performed as “strobe comparison”. Strobe is placed 5% before the end of the period. For the open-drain output (i.e. pin 51, LD), comparison to the “High-Impedance” state may be masked for some vectors.
5. Input voltages
During input voltage test, outputs are loaded with an active current load (when specified) and a capacitive load < 62 pF (tester load). For the active current load, the threshold load switching is set to $V_{DD}/2$.
Measurements are performed using the test pattern *main_pattern* (between the labels “main_st” and “end_u_d”). The pattern is run with increasing or decreasing input voltage value of the pin under test until the first output fails. Remaining pins toggle with nominal input voltages.
All the values are tested and recorded for each input.
The measurement accuracy is better than 100mV.
6. Output voltages
Measurements are performed using the test pattern *main_pattern*.
The device is configured into correct state so that outputs are placed in high or low voltages. Output current is sourced/sunk and the resulting voltage is measured.
All the values are tested and recorded for each output.
7. High impedance leakage current
The device is configured into the correct state using the pattern *main_pattern* so that the pin under test is in high impedance conditions (i.e. stop at label “llzhh”).
All the values are tested and recorded for each output.
8. Test patterns
Number of vectors (clock periods) for patterns used during test are:
 - *main_pattern* 117065 vectors @ 1 MHz (period = 1000ns) and 10 MHz (period = 100ns)
 - *dsm_p1* 1806 vectors @ 1 MHz (period = 1000ns)
 - *mode* 238 vectors @ 1 MHz (period = 1000ns)

9. Timing generators

All inputs use DATA mode timing generators (i.e. NRZ mode with zero delay) unless otherwise specified. The table below describes the timing generators. All patterns use the same set of timing generators:

Timing Generator Number	Period (ns)	Pin Group	Delay (ns)	Width (ns)	Comp. Start (ns)	Comp. Stop (ns)	Format
0	1000	1 to 3	0	-	-	-	NRZ
		4 to 7	-	-	-	900	EDGE
1	1000	1	0	-	-	-	NRZ
		2 and 3	100	-	-	-	NRZ
		4 to 7	-	-	-	950	EDGE
2	1000	1 (except SCLK pin)	0	-	-	-	NRZ
		SCLK pin	250	-	-	-	NRZ
		2 and 3	100	-	-	-	NRZ
		4 to 7	-	-	-	950	EDGE
3	1000	1	0	-	-	-	NRZ
		2 and 3	100	-	-	-	NRZ
		4 to 7	-	-	-	950	EDGE
4	1000	1	0	-	-	-	NRZ
		2 and 3	100	-	-	-	NRZ
		4 to 7	-	-	-	950	EDGE
5	100	1 (except SCLK pin)	0	-	-	-	NRZ
		SCLK pin	25	-	-	-	NRZ
		2 and 3	10	-	-	-	NRZ
		4 to 7	-	-	-	95	EDGE
6	1000	1	0	-	-	-	NRZ
		2 and 3	100	-	-	-	NRZ
		4 to 7	-	-	-	950	EDGE
7	1000	1 and 2	0	-	-	-	NRZ
		3	100	-	-	-	NRZ
		4 to 7	-	-	-	950	EDGE

Timing Generator Number	Period (ns)	Pin Group	Delay (ns)	Width (ns)	Comp. Start (ns)	Comp. Stop (ns)	Format
8	1000	1 (except S_WR, S_CLK and SDATA pins)	0	-	-	-	NRZ
		S_WR pin	600	-	-	-	NRZ
		SCLK pin	250	-	-	-	NRZ
		SDATA pin	100	-	-	-	NRZ
		2 and 3	100	-	-	-	NRZ
		4 to 7	-	-	-	950	EDGE
10	1000	1	0	-	-	-	NRZ
		2 and 3	100	-	-	-	NRZ
		4 to 7	-	-	-	950	EDGE
11	1000	1	0	-	-	-	NRZ
		2 and 3	100	-	-	-	NRZ
		4 to 7	-	-	-	950	EDGE
12		1 (except E_WR, S_CLK and SDATA pins)	0	-	-	-	NRZ
		E_WR pin	100	-	-	-	NRZ
		SCLK pin	150	-	-	-	NRZ
		SDATA pin	10	-	-	-	NRZ
		2 and 3	100	-	-	-	NRZ
		4 to 7	-	-	-	950	EDGE

10. Dynamic measurements

Parameters shall be measured and recorded for each dynamic parameter to be tested. The measurement accuracy is better than 0.5ns.

11. RF measurements

The frequency is set to the target frequency and output level at the FIN pin. The resulting output power is measured on DOUT.

The measurement accuracy is better than 0.1dB.

12. Phase Noise measurements

The Phase Noise measurements use a “Stack-and-Rack” solution. The parametric test settings are described hereafter:

- $f_{IN} = 1920.4$ MHz
- $f_r = 100$ MHz (0dBm)
- $f_c = 20$ MHz
- Loop Bandwidth = 50 kHz
- Register M = 8
- Register R = 4
- Register A = 6
- Register K = 5243
- Modulus = 10

13. Operating current during Phase Noise measurement

The parametric test settings are described in Note 12 above.

2.3.2 High and Low Temperatures Electrical Measurements

The measurements shall be performed at $T_{amb} = +85 (+0 -5) ^\circ\text{C}$ and $T_{amb} = -40 (+5 -0) ^\circ\text{C}$.

The characteristics, test methods, conditions and limits shall be the same as specified for Room Temperature Electrical Measurements, except as follows:

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions	Limits		Units
				Min	Max	
Standby Supply Current with Prescaler	I_{DDQ1}	3005	$V_{DD} = 3.45\text{V}$, $V_{SS} = 0\text{V}$ Use pattern <i>mode</i> , stop at label <i>pdwn_sp</i>	-	1000	μA

2.4 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3 ^\circ\text{C}$.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits	Limits		Units	
			Drift Value Δ	Absolute		
				Min		Max
Supply Current during Phase Noise Measurements, Typical High V_{DD}	I_{DDOPP2}	$\pm 10\%$	5	80	mA	
CMOS Output Voltage, Low Level (High Current Buffer at Minimum V_{DD})	V_{OL1_H}	± 50	-	400	mV	

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
CMOS Output Voltage, High Level (High Current Buffer at Minimum V_{DD})	V_{OH1_H}	± 0.1	2.25	-	V
Prescaler Input Sensitivity (Medium $1 f_{IN}$)	S_{FIN300}	± 2	-	-5	dBm

2.5 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3 \text{ }^\circ\text{C}$.

The characteristics, test methods, conditions and limits shall be as specified for Room Temperature Electrical Measurements.

2.6 POWER BURN-IN CONDITIONS

2.6.1 Electrical Test Conditions

Electrical test conditions shall be in accordance with the table below:

Characteristics	Symbols	Test Conditions	Units
Core Supply Voltage	V1	3.45 (+0 -5%)	V
Output Bias Voltage	V2	1.725 ($\pm 5\%$)	V
Input Voltage (Digital Inputs)	V_{IN}	0 to V1	V
Vector Length	t_0	1	μs

2.6.2 Environmental Test Conditions

Environmental test conditions shall be in accordance with the table below:

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+125 (+0 -5)	$^\circ\text{C}$

2.6.3 Burn-in Stimulus

The device shall be burned-in using “functional” vectors.

The Burn-in stimulus shall be made with vectors looping indefinitely. Each vector shall be made with thirteen (13) drivers. Each driver uses DATA mode, i.e. Non Return to Zero (NRZ) mode with toggling at the beginning of the vector. Looping this burn-in pattern exercises the PLL and PD_U/PD_D outputs toggle.

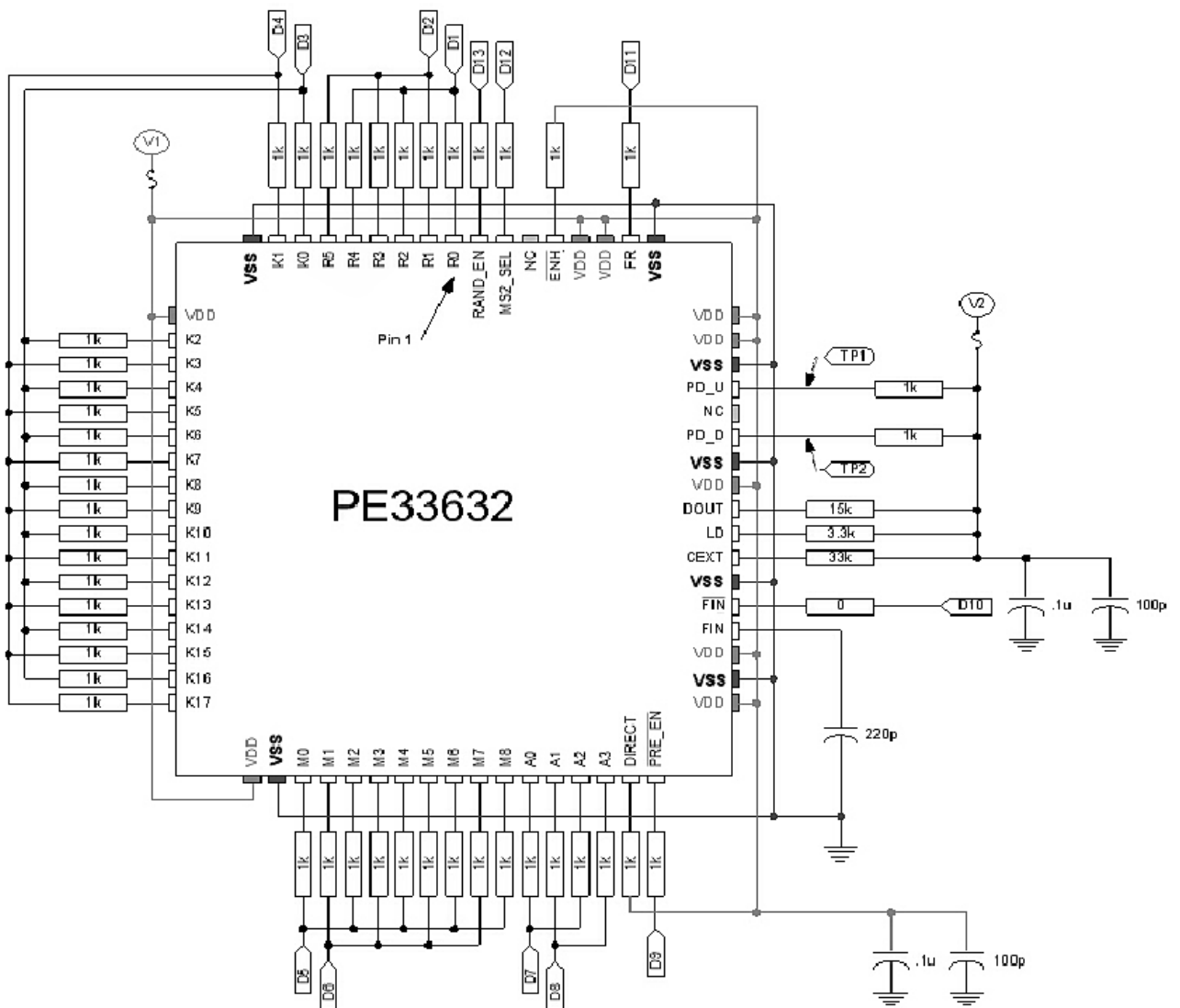
The device shall be set up in direct mode and counters loaded with checkerboard values in such a way that the PD_U and PD_D pins toggle alternately. The device shall go sequentially through seven (7) by-pass modes and sixteen (16) normal modes. Each mode includes eighty-six (86) vectors or forty-three (43) FIN clock cycles. FR (resp. MS2_SEL and RND_SEL) toggles every 11 (resp. 19 and 13) periods of FIN. There shall be 1978 vectors.

PRE_EN	A (hex)	K (hex)	M (hex)	R (hex)	FIN/FR ratio
By-pass mode					
1	-	-	155	2A	7.95
1	-	-	155	15	15.55
1	-	-	AA	2A	3.98
1	-	-	AA	15	7.77
1	-	-	1FF	15	23.27
1	-	-	1FF	3F	8
1	-	-	1FF	2A	11.91
Normal mode					
0	5	15555	155	15	155.7
0	5	15555	155	2A	79.66
0	5	15555	AA	15	77.97
0	5	15555	AA	2A	38.89
0	5	2AAAA	155	15	155.71
0	5	2AAAA	155	2A	79.67
0	5	2AAAA	AA	15	77.98
0	5	2AAAA	AA	2A	39.9
0	A	15555	155	15	155.92
0	A	15555	155	2A	79.78
0	A	15555	AA	15	78.2
0	A	15555	AA	2A	40.01
0	A	2AAAA	155	15	155.94

PRE_EN	A (hex)	K (hex)	M (hex)	R (hex)	FIN/FR ratio
0	A	2AAAA	155	2A	79.78
0	A	2AAAA	AA	15	78.21
0	A	2AAAA	AA	2A	40.02

2.6.4 Burn-in Schematic

The following schematic shows a suitable burn-in configuration for a single socket.



NOTES:

1. V1 is connected via a 500mA fuse.
2. V2 is connected via a 100mA fuse.
3. All resistors have a tolerance of $\pm 1\%$. All capacitors have a tolerance of $\pm 10\%$.
4. D1, D2, D3 etc. are Driver Numbers.
5. TP1 and TP2 are the Test Probes.

2.7 OPERATING LIFE CONDITIONS

The conditions shall be as specified for Power Burn-in.

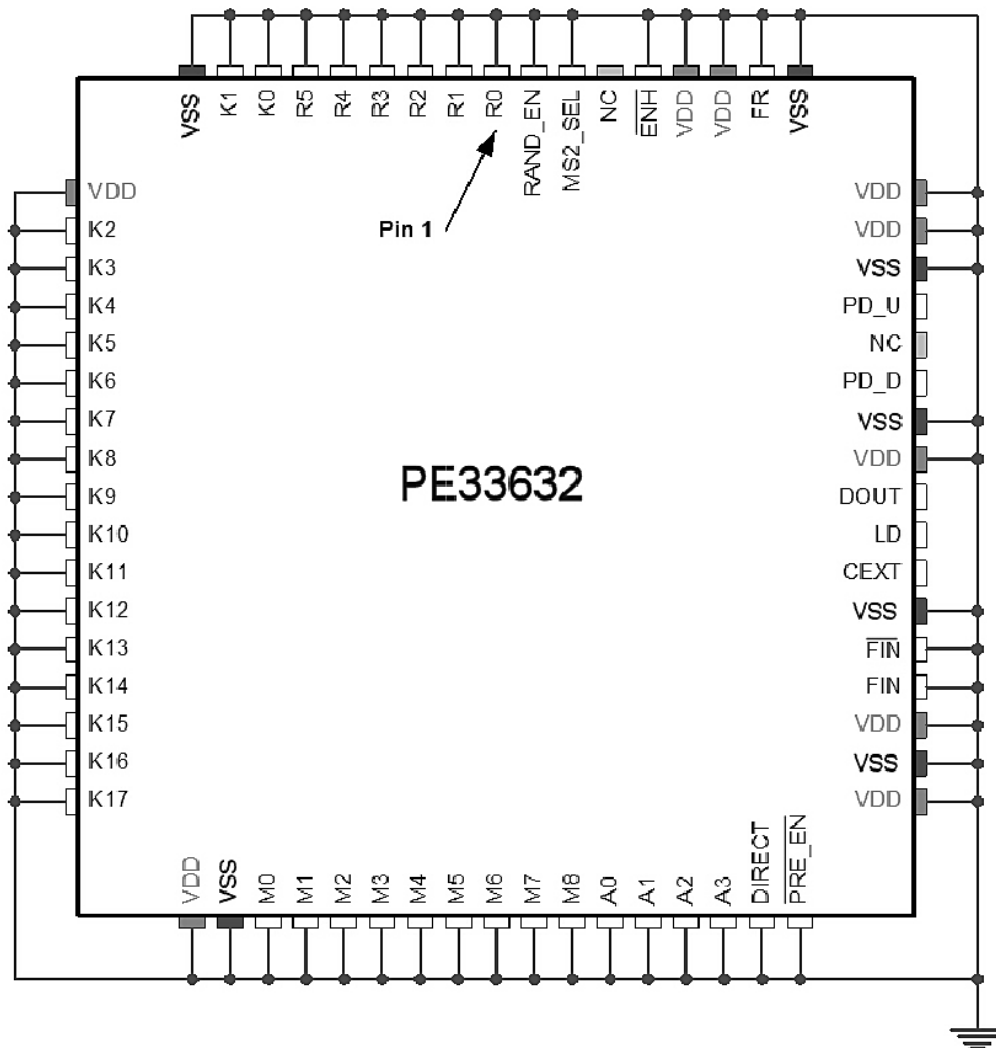
2.8 TOTAL DOSE RADIATION TESTING

2.8.1 Bias Conditions and Total Dose Level for Total Dose Radiation Testing

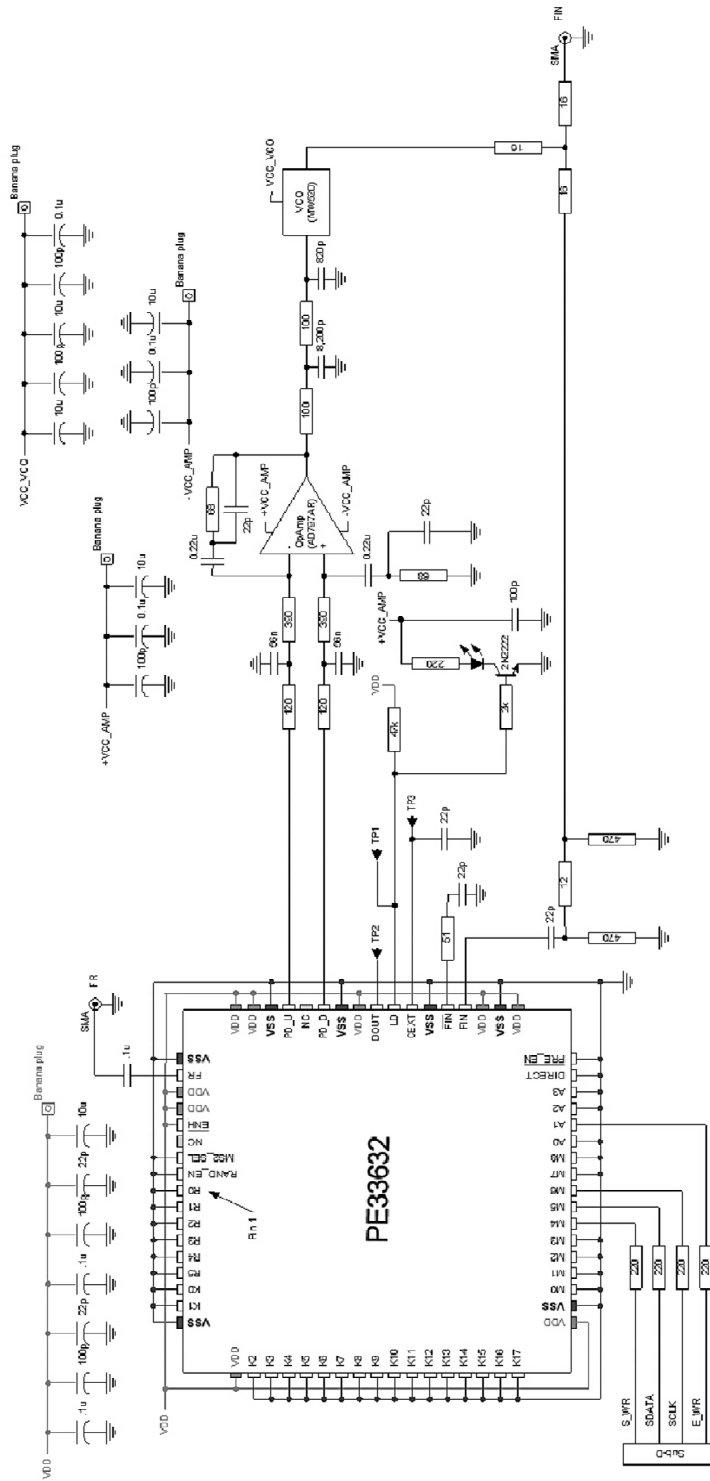
Bias shall be applied during irradiation testing as specified below.

The total dose level applied shall be as specified in the component type variant information herein or in the Purchase Order.

The following schematic shows a suitable test configuration for a single socket in unbiased condition (OFF).



The following schematic shows a suitable test configuration for a single socket in biased condition (ON).



NOTES:

1. $V_{DD} = 3.3V$, $V_{CC_VCO} = 5 \pm 0.2V$, $+V_{CC_AMP} = 5V$ and $-V_{CC_AMP} = -5V$.
2. $f_r = 40\text{ MHz}$, $V_P = V_{SS}$ to V_{DD} .
3. $f_{IN} = 1920.4\text{ MHz}$, $V_P = V_{SS}$ to V_{DD} .
4. All resistors have a tolerance of $\pm 1\%$. All capacitors have a tolerance of $\pm 10\%$.
5. TP1, TP2 and TP3 are the Test Probes.

6. The table below shows how the device shall be serially programmed during Total Dose Radiation Testing so the f_{IN} frequency is 1920.4 MHz.

Description	Value
R Counter	1
K Counter	5243
M Counter	8
A Counter	6
Reference Frequency	40 MHz

2.8.2 Electrical Measurements for Total Dose Radiation Testing

Unless otherwise specified the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

The characteristics, test methods, conditions and limits shall be as specified for Room Temperature Electrical Measurements.

APPENDIX 'A'
AGREED DEVIATIONS FOR PEREGRINE SEMICONDUCTOR EUROPE

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Deviations from Wafer Lot Acceptance - Chart F2	The SEM inspection may be performed using the specified ESCC Method or, alternatively, may be carried out in accordance with the requirements of MIL-STD-883 Test Method 2018.
Deviations from Screening Tests - Chart F3	<p>Following the PIND test, a Seal Test (Fine and Gross Leak) shall be performed in accordance with MIL-STD-883 Test Method 1014. An External Visual Inspection shall then be performed in accordance with ESCC Basic Specification No. 20500.</p> <p>Initial High and Low Temperatures Electrical Measurements may be performed prior to Burn-in at the option of the Manufacturer.</p> <p>The Check for Lot Failure shall only take into account any failures during Room Temperature Electrical Measurements. The number of failed components shall not exceed 5% of the components submitted to Burn-in.</p> <p>Room Temperature Electrical Measurements may be performed after Seal Test (Fine and Gross Leak).</p> <p>Radiographic Inspection shall be performed in accordance with ESCC Basic Specification No. 20900. The Manufacturer may perform the inspection at any point during Screening Tests subsequent to Serialisation.</p>
Deviations from Qualification and Periodic Tests - Chart F4	Permanence of Marking shall not be performed on devices which have been laser marked.